

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

Claims 1 to 9. (Canceled).

10. (Currently Amended) A magnetoresistive layer system comprising:
a magnetoresistive layer stack that works substantially on the basis of one of
a GMR effect and an AMR effect;
a layer array for generating a magnetic field which acts upon the
magnetoresistive layer stack, the layer array situated at least one of (a) on and (b)
below a magnetoresistive region of the magnetoresistive layer stack and including at
least one hard magnetic layer and at least one soft magnetic layer.

11. (Previously Presented) The magnetoresistive layer system according to
claim 10, wherein the hard magnetic layer and the soft magnetic layer are
ferromagnetically exchange coupled.

Claim 12. (Canceled).

13. (Previously Presented) The magnetoresistive layer system according to
claim 10, wherein the layer array has a plurality of soft magnetic layers and a
plurality of hard magnetic layers, which are combined into layer pairs having a hard
magnetic layer and an adjacent soft magnetic layer.

14. (Previously Presented) The magnetoresistive layer system according to
claim 10, wherein the soft magnetic layer is composed of a CoFe alloy, Co, Fe, Ni,
an FeNi alloy, and magnetic alloys which contain these materials.

15. (Previously Presented) The magnetoresistive layer system according to
claim 10, wherein the soft magnetic layer has a thickness between 1 nm and 50 nm.

16. (Previously Presented) The magnetoresistive layer system according to claim 15, wherein the thickness is between 1 nm and 10nm.

17. (Previously Presented) The magnetoresistive layer system according to claim 10, wherein the hard magnetic layer is composed of one of a CoCrPt alloy, a CoSm alloy, a CoCr alloy, a CoCrTa alloy, a CoPt alloy, and an FePt alloy.

18. (Previously Presented) The magnetoresistive layer system according to claim 10, wherein a thickness of the hard magnetic layer is between 20 nm and 100 nm.

19. (Currently Amended) A sensor element comprising:
a magnetoresistive layer system, in an environment of a magnetoresistive layer stack that works substantially on the basis of one of a GMR effect and an AMR effect, the magnetoresistive layer system including:
a layer array for generating a magnetic field which acts upon the magnetoresistive layer stack, the layer array situated at least one of (a) on and (b) below a magnetoresistive region of the magnetoresistive layer stack and including at least one hard magnetic layer and at least one soft magnetic layer.

20. (Previously Presented) The sensor element according to claim 19, wherein the sensor element is for detecting magnetic fields with respect to at least one of strength and direction.